

N-channel TrenchMOS logic level FET Rev. 04 — 8 July 2010

**Product data sheet** 

Suitable for logic level gate drive

Switched-mode power supplies

sources

#### **Product profile** 1.

#### **1.1 General description**

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

#### 1.2 Features and benefits

Simple gate drive required due to low gate charge

#### **1.3 Applications**

DC-to-DC convertors

#### 1.4 Quick reference data

#### Quick reference data Table 1

Table 1.	Quick reference da	la				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{DS}}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	30	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	43.4	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	57.6	W
Static cha	aracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$\label{eq:GS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 25 \text{ °C}; \text{ see } \underline{\text{Figure 9}}; \\ \text{see } \underline{\text{Figure 10}} \end{array}$	-	14	17	mΩ
Dynamic	characteristics					
Q <sub>GD</sub>	gate-drain charge		-	2.9	-	nC

# nexperia

#### N-channel TrenchMOS logic level FET

### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source <sup>[1]</sup>		
mb	D	mounting base; connected to drain		mbb076 S
			SOT78 (TO-220AB)	

[1] It is not possible to make a connection to pin 2.

### 3. Ordering information

#### Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PHP36N03LT	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

I<sub>SM</sub>

173.6 A

-

N-channel TrenchMOS logic level FET

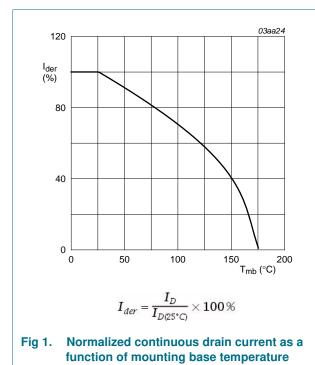
### 4. Limiting values

#### Table 4. Limiting values

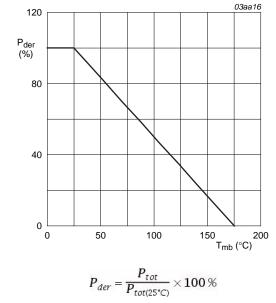
In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Min	Max	Unit
drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	30	V
drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	30	V
gate-source voltage		-20	20	V
drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	-	30.7	А
	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	43.4	A
peak drain current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; see <u>Figure 3</u>	-	173.6	А
total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	57.6	W
storage temperature		-55	175	°C
junction temperature		-55	175	°C
diode				
source current	T <sub>mb</sub> = 25 °C	-	43.4	А
	drain-source voltage         drain-gate voltage         gate-source voltage         drain current         peak drain current         total power dissipation         storage temperature         junction temperature         diode	$\begin{array}{ll} \mbox{drain-source voltage} & T_j \geq 25 \ {}^\circ\mbox{C}; \ T_j \leq 175 \ {}^\circ\mbox{C} \\ \mbox{drain-gate voltage} & T_j \geq 25 \ {}^\circ\mbox{C}; \ T_j \leq 175 \ {}^\circ\mbox{C}; \ R_{GS} = 20 \ k\Omega \\ \mbox{gate-source voltage} \\ \mbox{drain current} & V_{GS} = 10 \ V; \ T_{mb} = 100 \ {}^\circ\mbox{C}; \ see \ Figure 1} \\ \ V_{GS} = 10 \ V; \ T_{mb} = 25 \ {}^\circ\mbox{C}; \ see \ Figure 1}; \\ \ see \ Figure 3 \\ \mbox{pulsed}; \ t_p \leq 10 \ \mu\mbox{s}; \ T_{mb} = 25 \ {}^\circ\mbox{C}; \\ \ see \ Figure 3 \\ \ total \ power \ dissipation \\ \ T_{mb} = 25 \ {}^\circ\mbox{C}; \ see \ Figure 2 \\ \ storage \ temperature \\ \ junction \ temperature \\ \ diode \\ \end{array}$	$\begin{array}{c c c c c c } \mbox{drain-source voltage} & T_j \geq 25 \ {}^\circ\mbox{C}; \ T_j \leq 175 \ {}^\circ\mbox{C} & - & & & & & & & & & & & & & & & & & $	$\begin{array}{cccc} drain-source \ voltage & T_j \geq 25\ ^{\circ}C;\ T_j \leq 175\ ^{\circ}C & - & 30 \\ drain-gate \ voltage & T_j \geq 25\ ^{\circ}C;\ T_j \leq 175\ ^{\circ}C;\ R_{GS} = 20\ k\Omega & - & 30 \\ gate-source \ voltage & -20 & 20 \\ drain\ current & V_{GS} = 10\ V;\ T_{mb} = 100\ ^{\circ}C;\ see\ Figure\ 1 & - & 30.7 \\ V_{GS} = 10\ V;\ T_{mb} = 25\ ^{\circ}C;\ see\ Figure\ 1; & - & 43.4 \\ see\ Figure\ 3 & - & - & 43.4 \\ see\ Figure\ 3 & - & - & 173.6 \\ see\ Figure\ 3 & - & - & 57.6 \\ storage\ temperature & T_{mb} = 25\ ^{\circ}C;\ see\ Figure\ 2 & - & 57.6 \\ storage\ temperature & -55 & 175 \\ junction\ temperature & -55 & 175 \\ \end{array}$

pulsed;  $t_p \le 10 \ \mu s$ ;  $T_{mb} = 25 \ ^{\circ}C$ 



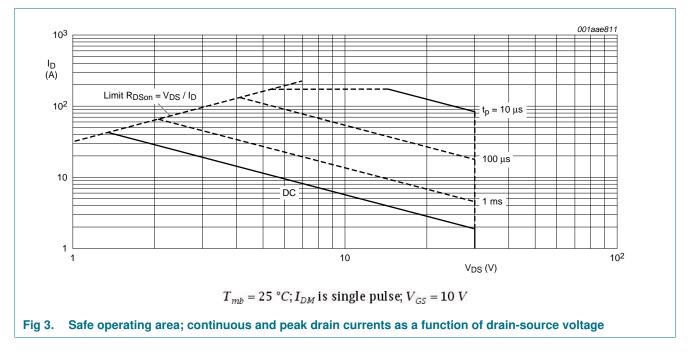
peak source current





# PHP36N03LT

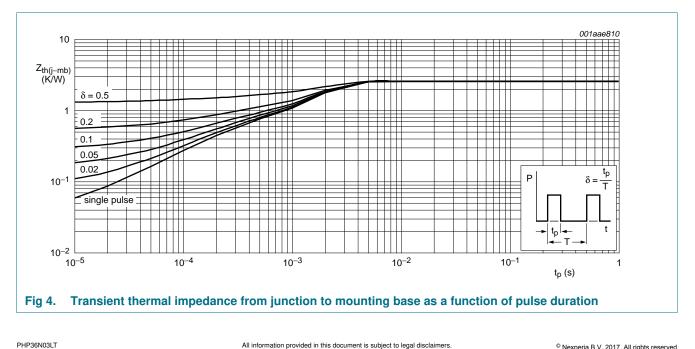
#### N-channel TrenchMOS logic level FET



#### **Thermal characteristics** 5.

#### Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th}(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	-	2.6	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W



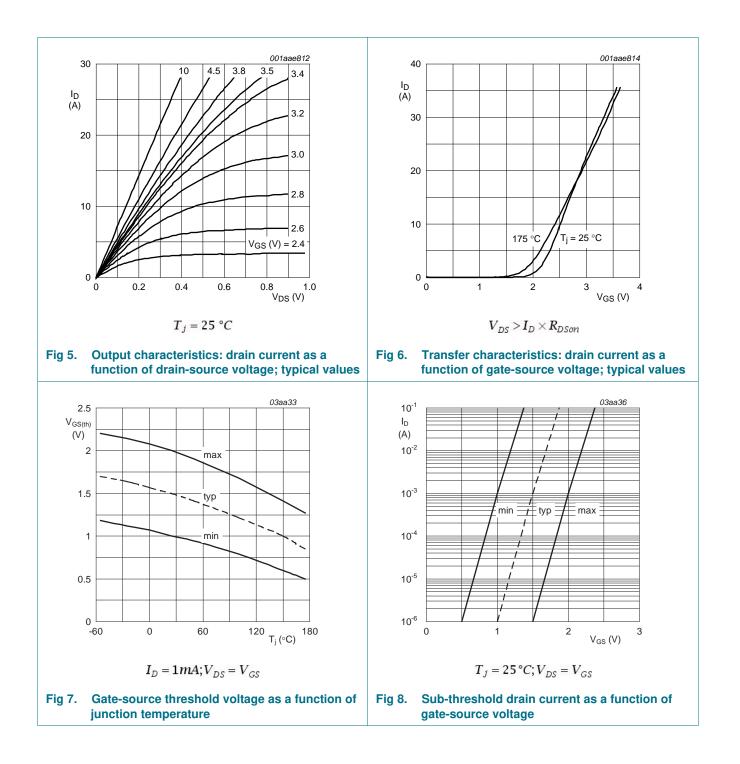
#### N-channel TrenchMOS logic level FET

### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub> drain-source		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	27	-	-	V
	breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	30	-	-	V
	gate-source threshold voltage	$I_D = 250 \ \mu\text{A}; V_{DS} = V_{GS}; T_j = 175 \ ^\circ\text{C};$ see <u>Figure 7</u> ; see <u>Figure 8</u>	0.5	-	-	V
		$I_D = 250 \ \mu\text{A}; V_{DS} = V_{GS}; T_j = 25 \ ^{\circ}\text{C};$ see <u>Figure 7</u> ; see <u>Figure 8</u>	1	1.5	2	V
		I <sub>D</sub> = 250 μA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <u>Figure 7</u> ; see <u>Figure 8</u>	-	-	2.2	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	1	μA
		$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
Boom	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	14	17	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 12 A; T <sub>j</sub> = 175 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	- 32.4	39.6	mΩ
		V <sub>GS</sub> = 3.5 V; I <sub>D</sub> = 5.2 A; T <sub>j</sub> = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	22	40	mΩ
		$V_{GS}$ = 4.5 V; $I_D$ = 12 A; $T_j$ = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	18	22	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 36 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$	-	18.5	-	nC
Q <sub>GS</sub>	gate-source charge	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 11}{\text{Figure } 12}; \text{ see } \frac{\text{Figure } 12}{\text{Figure } 12}$	-	4.2	-	nC
Q <sub>GD</sub>	gate-drain charge		-	2.9	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	690	-	pF
C <sub>oss</sub>	output capacitance	V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	160	-	pF
C <sub>rss</sub>	reverse transfer capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	110	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 15 \text{ V}; \text{ R}_{L} = 0.6 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	10	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	33	-	ns
t <sub>f</sub>	fall time		-	19	-	ns
Source-d	rain diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	0.97	1.2	V

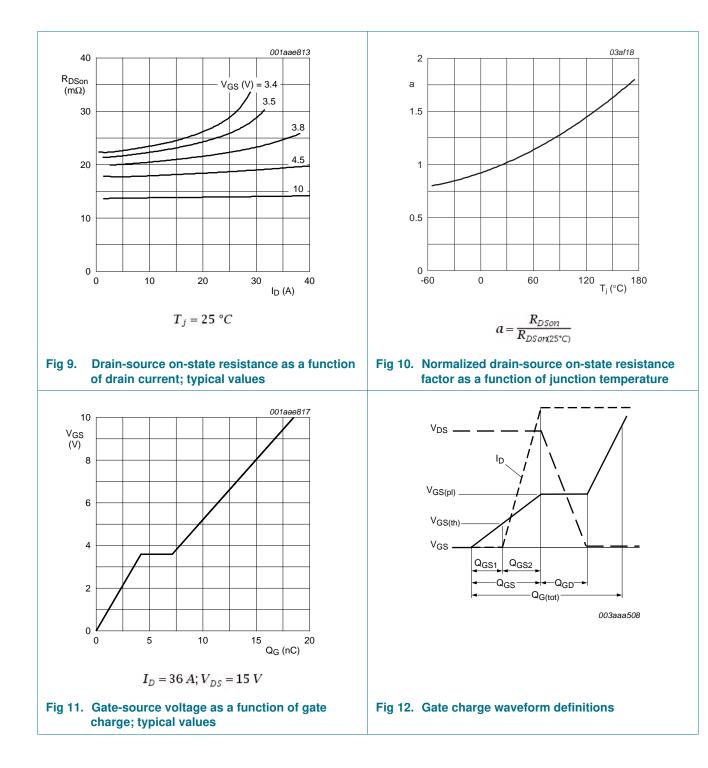
# PHP36N03LT

#### N-channel TrenchMOS logic level FET



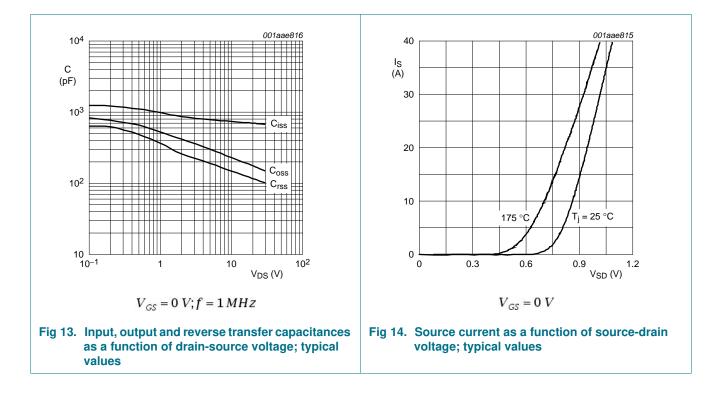
# PHP36N03LT

#### N-channel TrenchMOS logic level FET



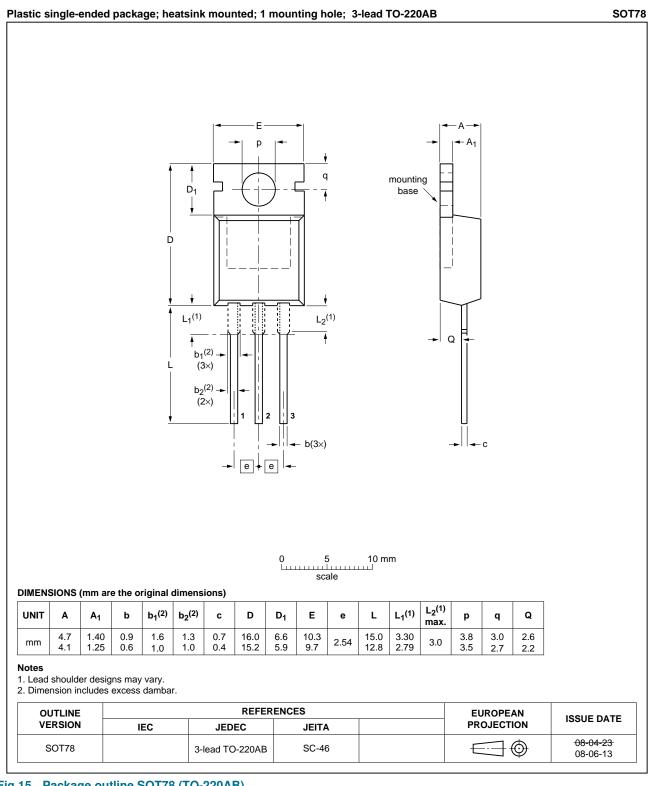
# PHP36N03LT

#### N-channel TrenchMOS logic level FET



#### N-channel TrenchMOS logic level FET

#### **Package outline** 7.



#### Fig 15. Package outline SOT78 (TO-220AB)

PHP36N03LT **Product data sheet** 

#### N-channel TrenchMOS logic level FET

### 8. Revision history

Table 7.Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PHP36N03LT v.4	20100708	Product data sheet	-	PHP36N03LT v.3
Modifications:	<ul> <li>Various changes</li> </ul>	s to content.		
PHP36N03LT v.3	20100329	Product data sheet	-	-

#### N-channel TrenchMOS logic level FET

#### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia</u>.com.

#### 9.2 Definitions

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

**Product specification** — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Nexperia and its customer, unless Nexperia and

customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Nexperia product is deemed to offer functions and qualities beyond those described in the Product data sheet.

#### 9.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Nexperia does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall Nexperia be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Nexperia's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Nexperia.

**Right to make changes** — Nexperia reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof. Suitability for use — Nexperia products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of a Nexperia product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Nexperia accepts no liability for inclusion and/or use of Nexperia products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. Nexperia makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Nexperia does not accept any liability related to any default, damage, costs or problem which is based on a weakness or default in the customer application/use or the application/use of customer's third party customer(s) (hereinafter both referred to as "Application"). It is customer's sole responsibility to check whether the Nexperia product is suitable and fit for the Application planned. Customer has to do all necessary testing for the Application in order to avoid a default of the Application and the product. Nexperia does not accept any liability in this respect.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding. Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

#### Terms and conditions of commercial sale - Nexperia

products are sold subject to the general terms and conditions of commercial sale, as published at <a href="http://www.nexperia.com/profile/terms">http://www.nexperia.com/profile/terms</a>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Nexperia hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Nexperia products by customer.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

Product data sheet

#### N-channel TrenchMOS logic level FET

**Non-automotive qualified products** — Unless this data sheet expressly states that this specific Nexperia product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. Nexperia accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without Nexperia's warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond Nexperia's specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies Nexperia for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond Nexperia's standard warranty and Nexperia's product specifications.

#### 9.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

### **10. Contact information**

For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: <u>salesaddresses@nexperia.com</u>

#### N-channel TrenchMOS logic level FET

#### 11. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values3
5	Thermal characteristics4
6	Characteristics5
7	Package outline9
8	Revision history10
9	Legal information11
9.1	Data sheet status11
9.2	Definitions11
9.3	Disclaimers
9.4	Trademarks12
10	Contact information12